

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown 10/600 965
		Filing Date	Even Date Herewith 6/20/03
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown 2813
		Examiner Name	Tran, Mai-Huong
Sheet 1 of 2		Attorney Docket No: 303.716US2	

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		Group Art Unit	Unknown - 2813
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Substitute for form 1449/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <small>(Use as many sheets as necessary)</small>		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>10/600965</td> </tr> <tr> <td>Filing Date</td> <td>June 20, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2813</td> </tr> <tr> <td>Examiner Name</td> <td>Tran, Mai-Huong</td> </tr> </table>					Application Number	10/600965	Filing Date	June 20, 2003	First Named Inventor	Ahn, Kie	Group Art Unit	2813	Examiner Name	Tran, Mai-Huong
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